Elektronische Bauelemente

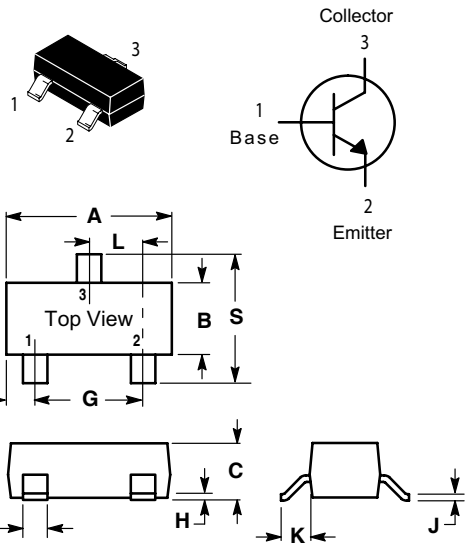
SS8050W

NPN Silicon
General Purpose Transistor

RoHS Compliant Product

FEATURES

Power dissipation
P_{CM} : 0.2 W
Collector Current
I_{CM} : 1.5 A
Collector-base voltage
$V_{(BR)CBO}$: 40 V
Operating & storage junction temperature
T_j, T_{stg} : - 55°C ~ + 150° C



SOT-323		
Dim	**Min**	**Max**
A	1.800	2.200
B	1.150	1.350
C	0.800	1.000
D	0.300	0.400
G	1.200	1.400
H	0.000	0.100
J	0.100	0.250
K	0.350	0.500
L	0.590	0.720
S	2.000	2.400
V	0.280	0.420
All Dimension in mm		

ELECTRICAL CHARACTERISTICS (Tamp.=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 100 μ A, I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 0.1mA, I_B=0	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100 μ A, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=40 V , I_E=0			0.1	μ A
Collector cut-off current	I_{CEO}	V_{CE}=20V , I_B=0			0.1	μ A
Emitter cut-off current	I_{EBO}	V_{EB}= 5V , I_C=0			0.1	μ A
DC current gain	$H_{FE(1)}$	V_{CE}=1V, I_C= 50mA	120		350	
	$H_{FE(2)}$	V_{CE}=1V, I_C=500mA	40			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=500 mA, I_B= 50mA			0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=500 mA, I_B= 50mA			1.2	V
Transition frequency	f_T	V_{CE}=6V, I_C= 20mA f=30MHz	100			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H
Range	120-200	200-350

Marking : Y1

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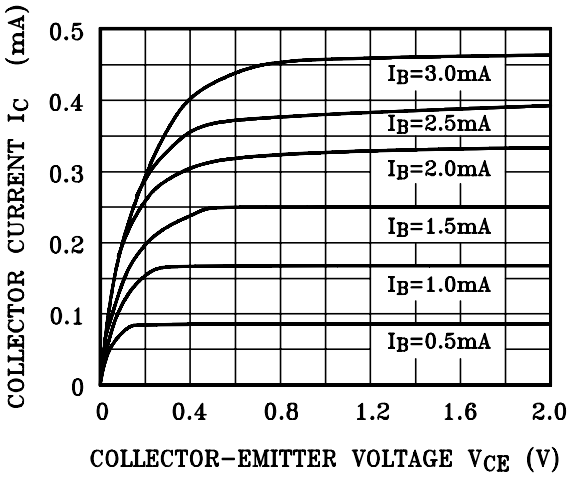
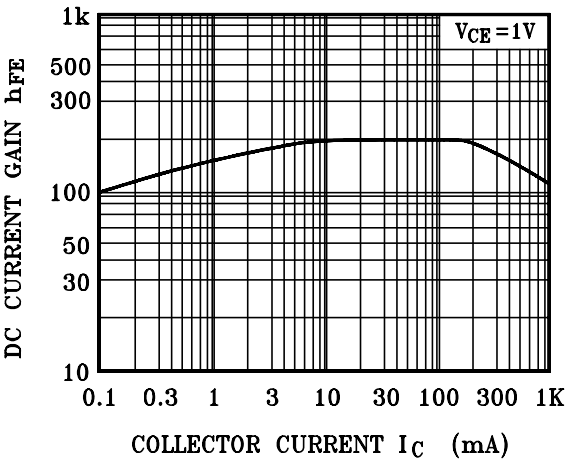
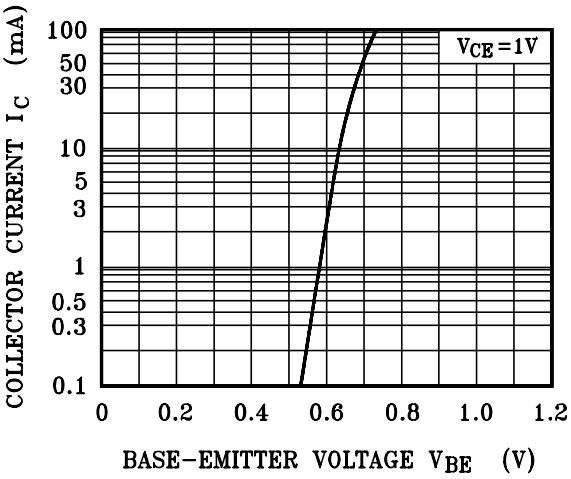
$I_C - V_{CE}$



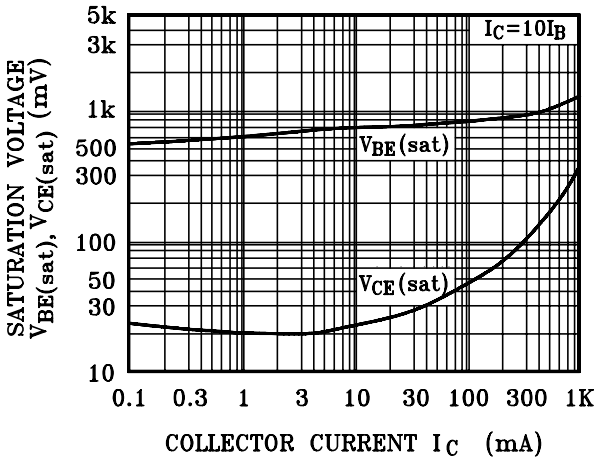
$h_{FE} - I_C$



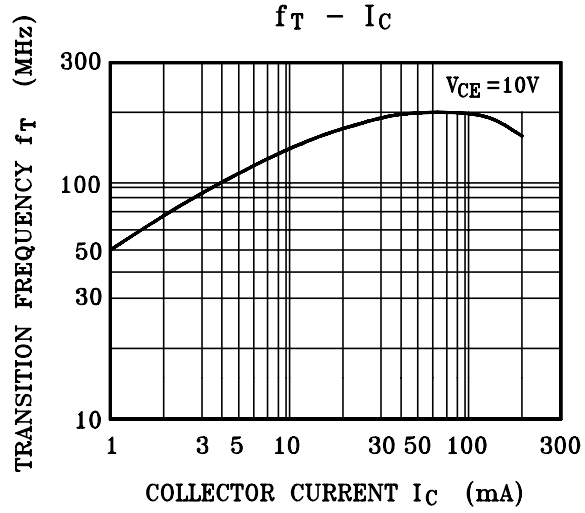
$I_C - V_{BE}$



$V_{BE(sat)}, V_{CE(sat)} - I_C$



$f_T - I_C$



$C_{ob} - V_{CB}$